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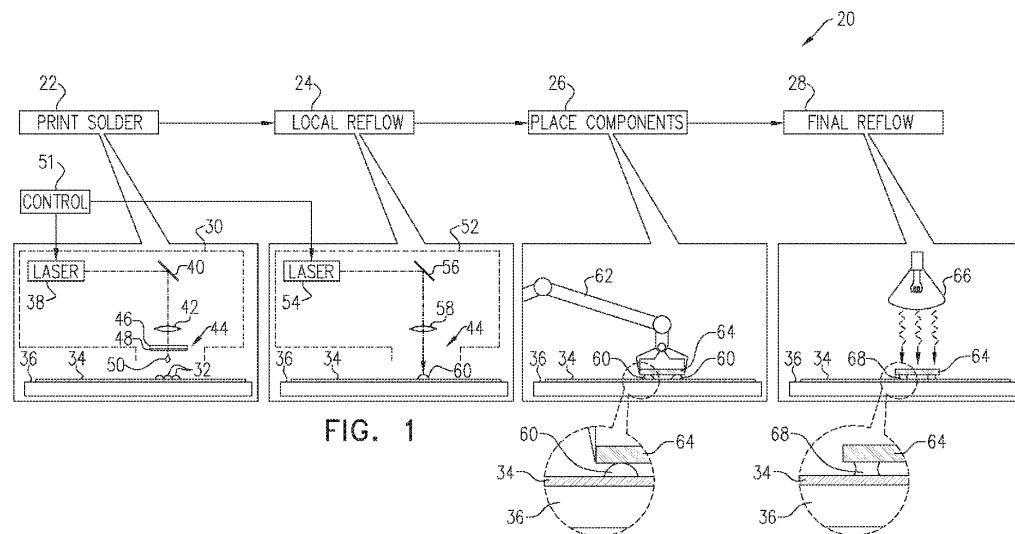
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(54) Title: HIGH-RESOLUTION SOLDERING



(57) Abstract: A method for circuit fabrication includes defining a solder bump, including a specified solder material and having a specified bump volume, to be formed at a target location on an acceptor substrate. A transparent donor substrate, having a donor film including the specified solder material, is positioned such that the donor film is in proximity to the target location on the acceptor substrate. A sequence of pulses of laser radiation is directed to pass through the first surface of the donor substrate and impinge on the donor film so as to induce ejection from the donor film onto the target location on the acceptor substrate of a number of molten droplets of the solder material such that the droplets deposited at the target location cumulatively reach the specified bump volume. The target location is heated so the deposited droplets melt and reflow to form the solder bump.

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